Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a SOT323 (SC-70) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low R_{DSon}
- Very fast switching
- Trench MOSFET technology

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} 25 °C	[1]	-	-	-1	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -1 A; T_j = 25 °C		-	175	200	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2	G
			SC-70 (SOT323)	017aaa094

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMF170XP	SC-70	plastic surface-mounted package; 3 leads	SOT323			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMF170XP	XD%

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} 25 °C	[1]	-	-1	А
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-0.7	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	290	mW
			[1]	-	360	mW
		$T_{sp} = 25 ^{\circ}C$		-	1670	mW
T _j	junction temperature			-55	150	°C

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Symbol	Parameter	Conditions		Min	Max	Unit	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-drain diode							
I _S	source current	T _{amb} = 25 °C	[1]	-	-0.4	Α	

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

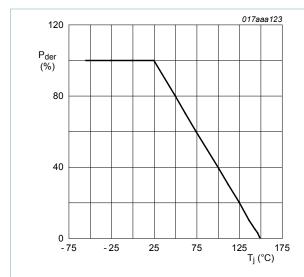


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

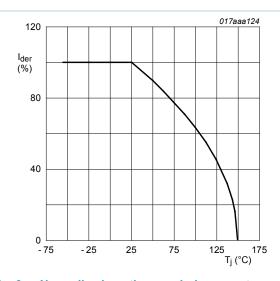
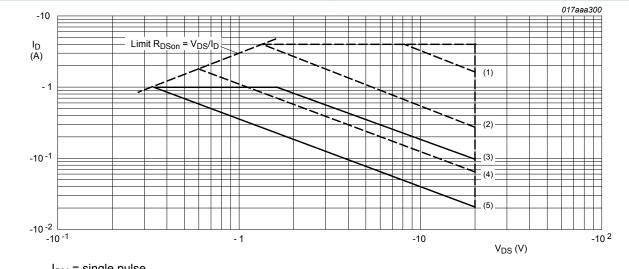


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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I_{DM} = single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) $t_p = 10 \text{ ms}$
- (3) DC; $T_{sp} = 25 \,^{\circ}\text{C}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; $T_{amb} = 25 \, ^{\circ}\text{C}$; drain mounting pad 6 cm²

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uig a)	thermal resistance from junction to ambient	in free air	[1]	-	377	430	K/W
			[2]	-	305	350	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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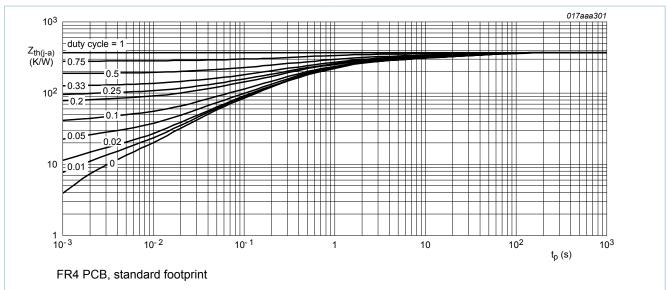


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

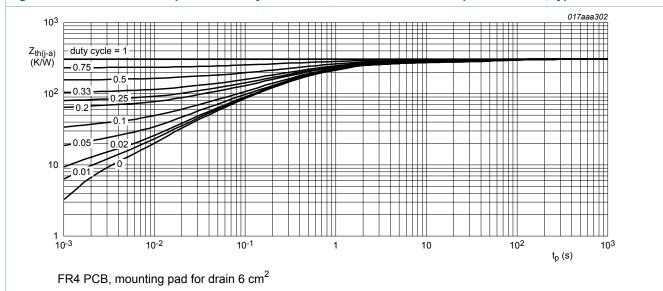


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Static chara	Static characteristics								
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V		
V_{GSth}	gate-source threshold voltage	I_D = -250 A; V_{DS} = V_{GS} ; T_j = 25 °C		-0.65	-0.9	-1.15	V		
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	-1	μΑ		
		V_{DS} = -20 V; V_{GS} = 0 V; T_j = 150 °C		-	-	-10	μA		
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
		V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_{D} = -1 A; T_{j} = 25 °C	-	175	200	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -1 A; T_j = 150 °C	-	250	284	mΩ
		V_{GS} = -2.5 V; I_{D} = -1 A; T_{j} = 25 °C	-	240	300	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; I_{D} = -1 \text{ A}; T_{j} = 25 \text{ °C}$	-	1.9	-	S
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -1 A; V_{GS} = -4.5 V; T_{j} = 25 °C	-	2.6	3.9	nC
Q _{GS}	gate-source charge		-	0.63	-	nC
Q_{GD}	gate-drain charge		-	0.53	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	280	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	43	-	pF
C _{rss}	reverse transfer capacitance		-	30	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -1 A; V_{GS} = -4.5 V;	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	16	-	ns
t _{d(off)}	turn-off delay time	1	-	31	-	ns
t _f	fall time	1	-	13	-	ns
Source-dra	nin diode		I			
V _{SD}	source-drain voltage	I _S = -0.4 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

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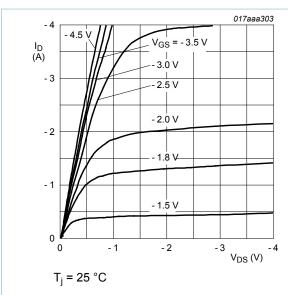
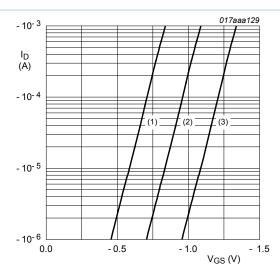


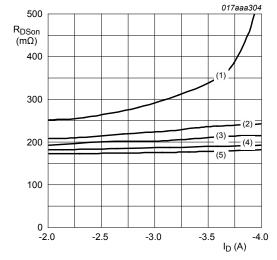
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = -3 \,^{\circ}\text{V}$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



$$(1) V_{GS} = -2.5 V$$

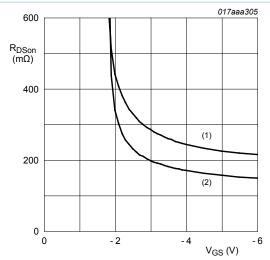
(2)
$$V_{GS} = -3.0 \text{ V}$$

$$(3) V_{GS} = -3.5 V$$

$$(4) V_{GS} = -4.0 V$$

$$(5) V_{GS} = -4.5 V$$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

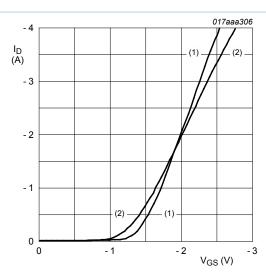


(1)
$$T_i = 150 \,^{\circ}C$$

(2)
$$T_i = 25 \, ^{\circ}C$$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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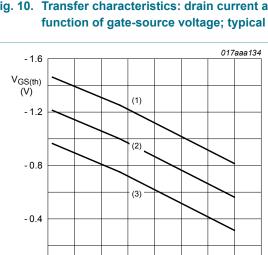


$$V_{DS} > I_{D} \times R_{DSon}$$

(1)
$$T_j = 25 \, ^{\circ}C$$

(2)
$$T_j = 150 \, ^{\circ}C$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

T_i (°C)

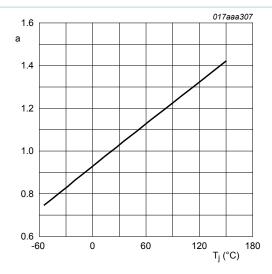
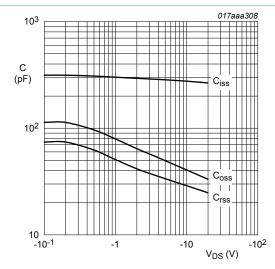


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

0.0

- 60

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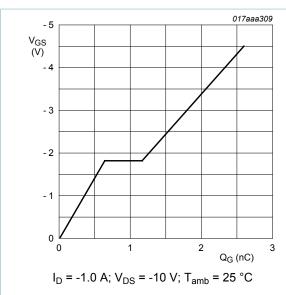


Fig. 14. Gate-source voltage as a function of gate charge; typical values

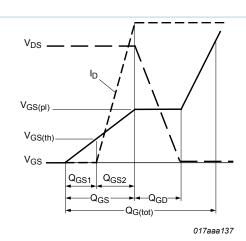
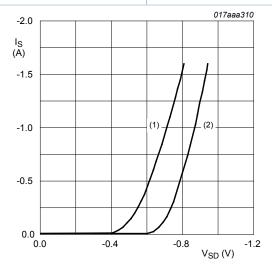


Fig. 15. Gate charge waveform definitions



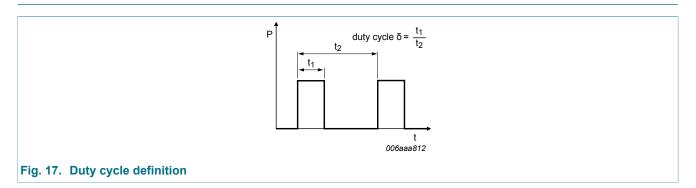
 $V_{GS} = 0 V$ (1) $T_j = 150 °C$ (2) $T_i = 25 °C$

Fig. 16. Source current as a function of source-drain voltage; typical values

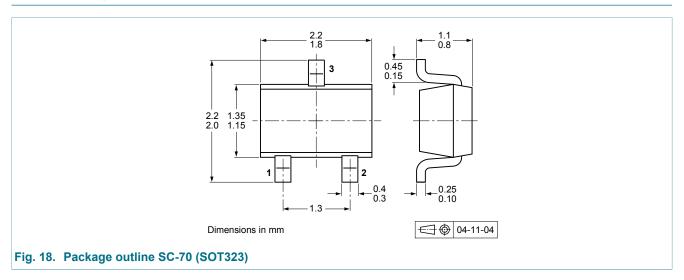
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11. Test information

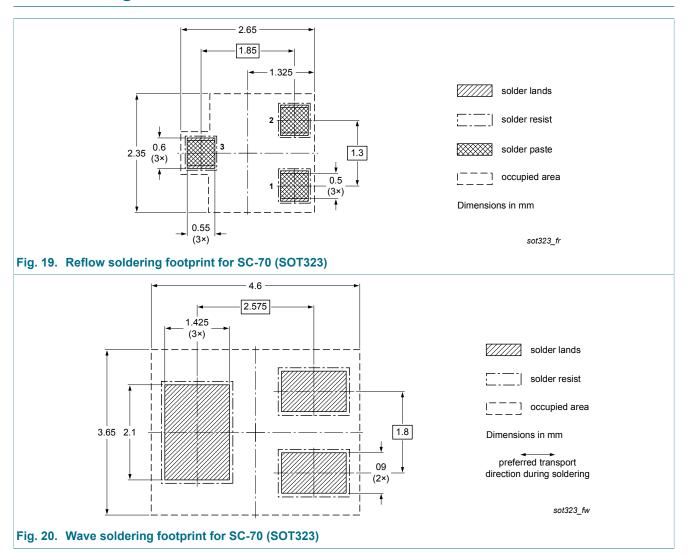


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMF170XP v.2	20131029	Product data sheet	-	PMF170XP v.1
Modifications:	Figure 13 corrected			
PMF170XP v.1	20110902	Product data sheet	-	-

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15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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